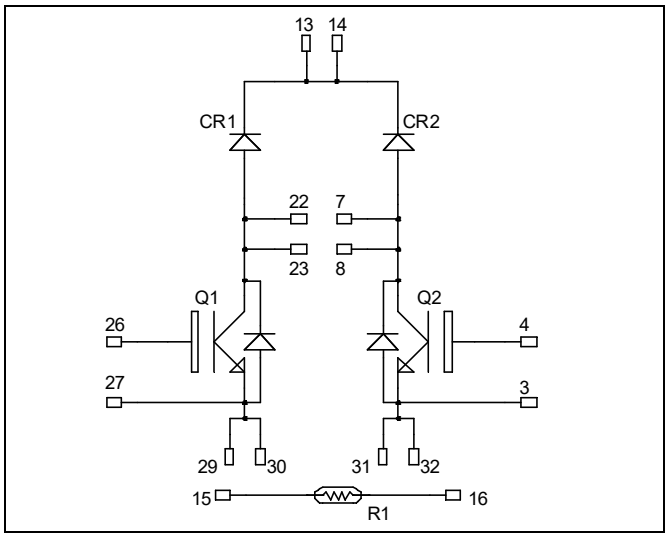
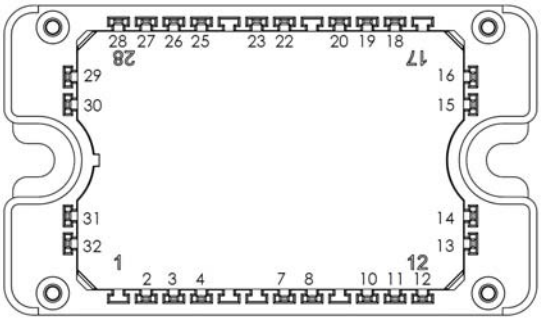
APTGT75DDA60T3G

Dual Boost chopper
Trench + Field Stop IGBT3
Power Module

V_{CES} = 600V
I_C = 75A @ Tc = 80°C





All multiple inputs and outputs must be shorted together
Example: 13/14 ; 29/30 ; 22/23 …

Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction

Features

- **Trench + Field Stop IGBT3**
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 20 kHz
  - Low leakage current
  - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
- Internal thermistor for temperature monitoring

Benefits

- Stable temperature behavior
- Very rugged
- Solderable terminals for easy PCB mounting
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Each leg can be easily paralleled to achieve a single boost of twice the current capability.
- RoHS Compliant

All ratings @ T_j = 25°C unless otherwise specified

Absolute maximum ratings (Per IGBT)

Symbol	*Parameter*		*Max ratings*	*Unit*
V_{CES}	Collector - Emitter Voltage		600	V
I_C	Continuous Collector Current	T_C = 25°C	100	A
		T_C = 80°C	75	
I_{CM}	Pulsed Collector Current	T_C = 25°C	140	
V_{GE}	Gate – Emitter Voltage		±20	V
P_D	Power Dissipation	T_C = 25°C	250	W
RBSOA	Reverse Bias Safe Operating Area	T_J = 150°C	150A @ 550V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

Electrical Characteristics (Per IGBT)

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	V_{GE} = 0V, V_{CE} = 600V				100	µA
$V_{CE(sat)}$	Collector Emitter Saturation Voltage	V_{GE} =15V I_C = 75A	T_j = 25°C		1.5	1.9	V
			T_j = 150°C		1.7		
$V_{GE(th)}$	Gate Threshold Voltage	V_{GE} = V_{CE}, I_C = 600µA		5.0	5.8	6.5	V
I_{GES}	Gate – Emitter Leakage Current	V_{GE} = 20V, V_{CE} = 0V				600	nA

Dynamic Characteristics (Per IGBT)

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
C_{ies}	Input Capacitance	V_{GE} = 0V V_{CE} = 25V f = 1MHz			4620		pF
C_{oes}	Output Capacitance				300		
C_{res}	Reverse Transfer Capacitance				140		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) V_{GE} = ±15V V_{Bus} = 300V I_C = 75A R_G = 4.7Ω			110		ns
T_r	Rise Time				45		
$T_{d(off)}$	Turn-off Delay Time				200		
T_f	Fall Time				40		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (150°C) V_{GE} = ±15V V_{Bus} = 300V I_C = 75A R_G = 4.7Ω			120		ns
T_r	Rise Time				50		
$T_{d(off)}$	Turn-off Delay Time				250		
T_f	Fall Time				60		
E_{on}	Turn-on Switching Energy	V_{GE} = ±15V V_{Bus} = 300V I_C = 75A R_G = 4.7Ω	T_j = 150°C		0.6		mJ
E_{off}	Turn-off Switching Energy		T_j = 150°C		2.6		mJ
R_{thJC}	Junction to Case Thermal Resistance					0.60	°C/W

Chopper diode ratings and characteristics (Per diode)

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V_{RRM}	Peak Repetitive Reverse Voltage					600	V
I_{RM}	Reverse Leakage Current	V_R=600V				250	µA
I_F	DC Forward current		Tc = 80°C		75		A
V_F	Diode Forward Voltage	I_F = 75A V_{GE} = 0V	T_j = 25°C		1.6	2	
			T_j = 150°C		1.5		V
t_{rr}	Reverse Recovery Time	I_F = 75A V_R = 300V di/dt =2000A/µs	T_j = 25°C		100		ns
			T_j = 150°C		150		
Q_{rr}	Reverse Recovery Charge		T_j = 25°C		3.6		µC
			T_j = 150°C		7.6		
E_r	Reverse Recovery Energy		T_j = 25°C		0.85		mJ
			T_j = 150°C		1.8		
R_{thJC}	Junction to Case Thermal Resistance					0.98	°C/W

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic		Min	Typ	Max	Unit
R_{25}	Resistance @ 25°C			50		kΩ
$\Delta R_{25}/R_{25}$				5		%
$B_{25/85}$	T_{25} = 298.15 K			3952		K
$\Delta B/B$		T_C=100°C		4		%

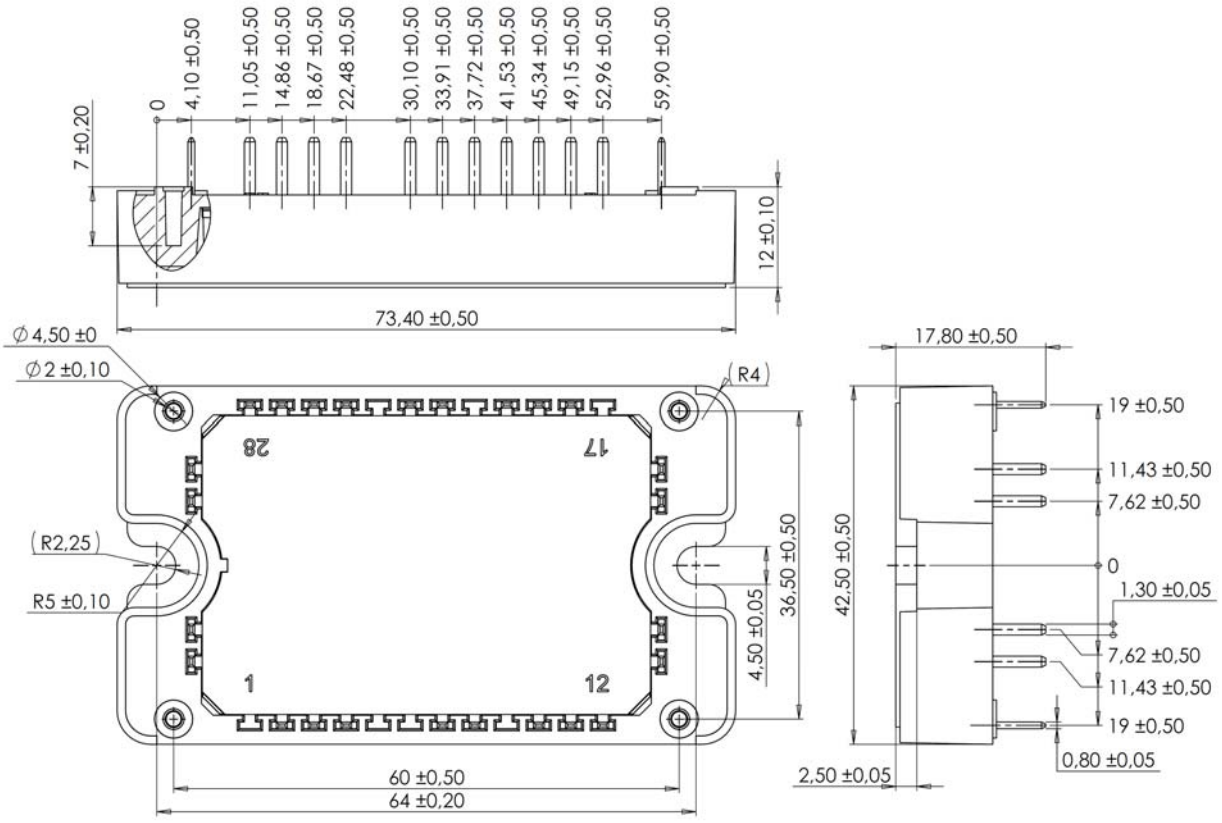
$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$

T: Thermistor temperature
R_T: Thermistor value at T

Thermal and package characteristics

Symbol	Characteristic			Min	Max	Unit
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000		V
T_J	Operating junction temperature range			-40	175	°C
T_{JOP}	Recommended junction temperature under switching conditions			-40	$T_J$max -25	
T_{STG}	Storage Temperature Range			-40	125	
T_C	Operating Case Temperature			-40	125	
Torque	Mounting torque	To heatsink	M4	2	3	N.m
Wt	Package Weight				110	g

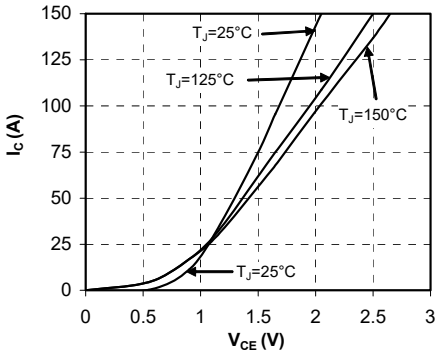
Package outline (dimensions in mm)



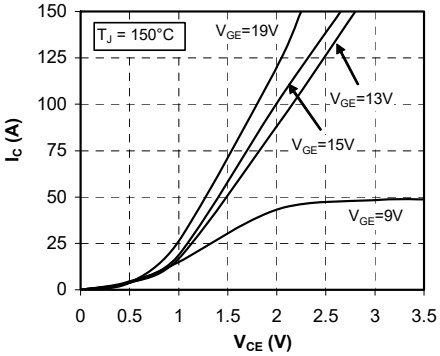
See application note 1906 - Mounting Instructions for SP3F Power Modules on www.microsemi.com

Typical Performance Curve

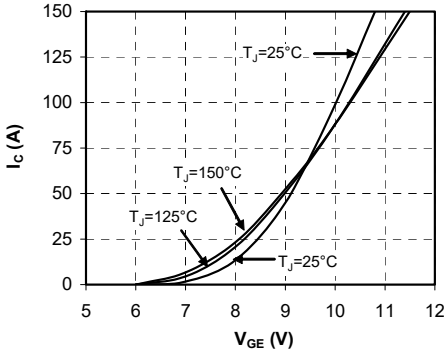
Output Characteristics (V_{GE}=15V)



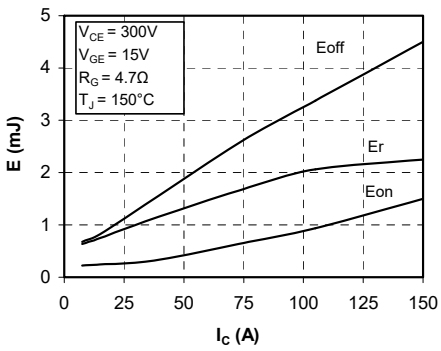
Output Characteristics



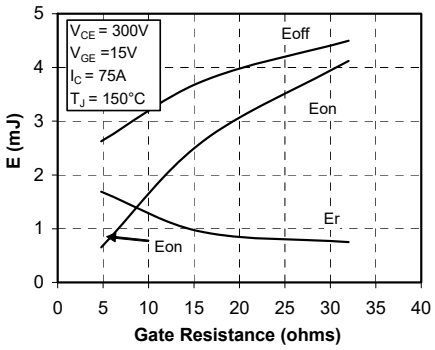
Transfert Characteristics



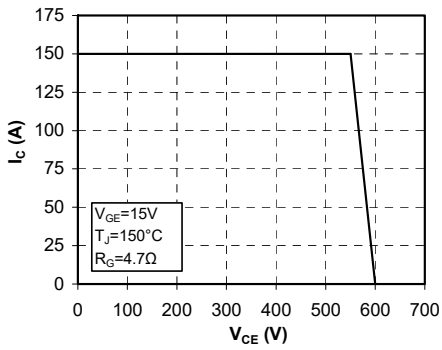
Energy losses vs Collector Current



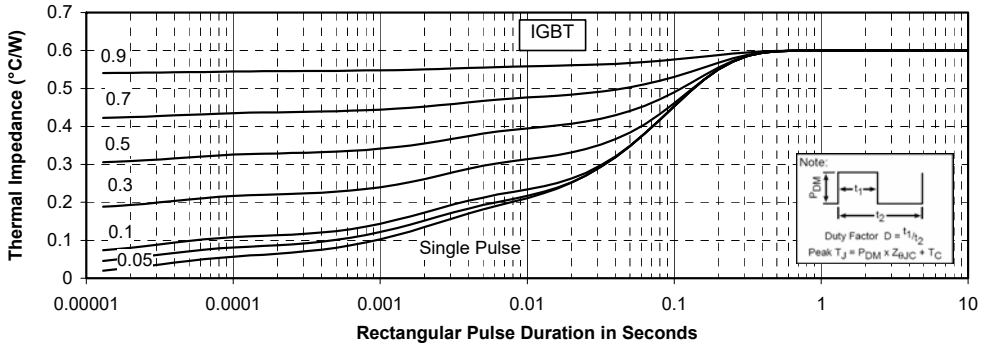
Switching Energy Losses vs Gate Resistance

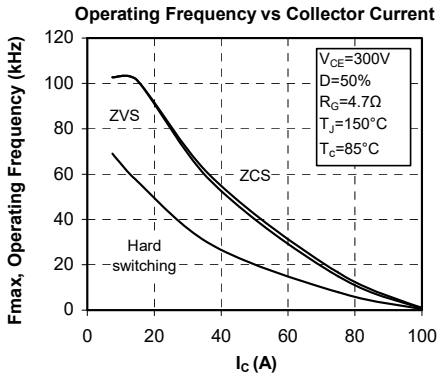


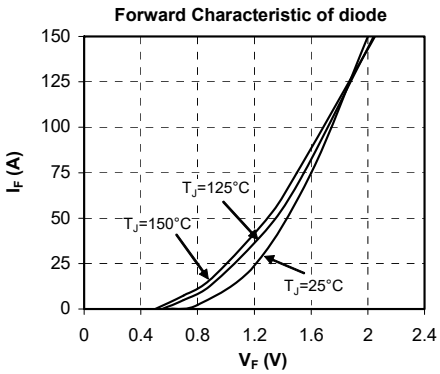
Reverse Bias Safe Operating Area

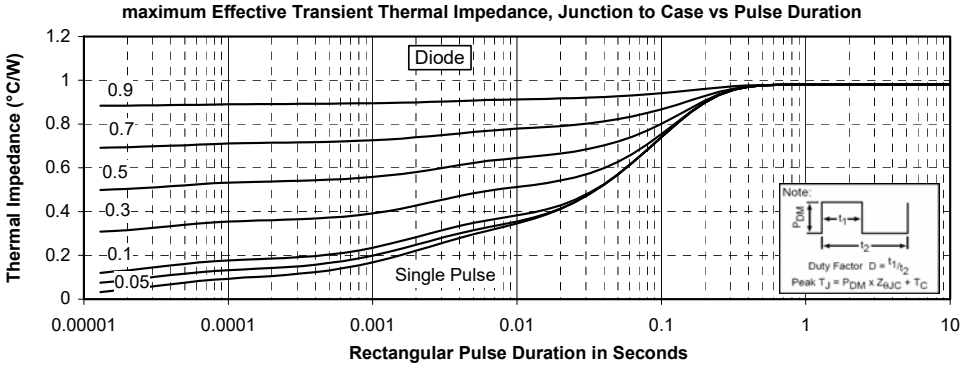


maximum Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration




Operating Frequency vs Collector Current
Fmax, Operating Frequency (kHz)
I_C (A)
V_{CE}=300V
D=50%
R_G=4.7Ω
T_J=150°C
T_c=85°C
ZVS
ZCS
Hard switching


Forward Characteristic of diode
I_F (A)
V_F (V)
T_J=125°C
T_J=150°C
T_J=25°C


maximum Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration
Thermal Impedance (°C/W)
Rectangular Pulse Duration in Seconds
Diode
0.9
0.7
0.5
0.3
0.1
0.05
Single Pulse
Note:
Duty Factor D = t_1/t_2
Peak T_J = P_{DM} x $Z_{\theta JC}$ + T_C

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